

1200V/40A IGBT WITH DIODE

General Description

DOSEMI IGBT Power Discrete provides ultralow conduction loss as well as low switching loss. They are designed for the applications such as solar power.

Features

- Low $V_{CE(sat)}$ Fast IGBT technology
- Low switching loss
- Maximum junction temperature 175°C
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Lead free package

Typical Applications

- Solar power
- UPS
- 3-level-application

